









Semiconductor device and manufacturing method thereof

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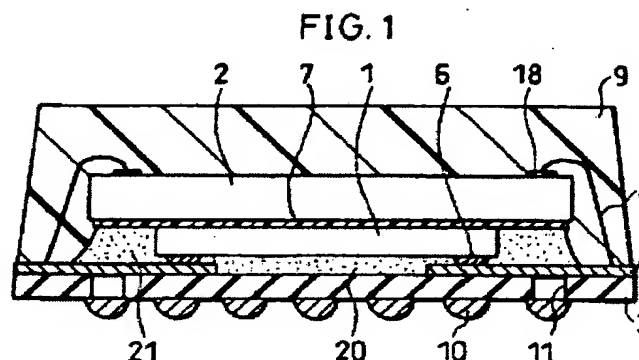
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Abstract of EP1045443

When a first semiconductor chip is installed on a circuit substrate by using an anisotropic conductive bonding agent, one portion thereof is allowed to protrude outside the first semiconductor chip. A second semiconductor chip is installed on the first semiconductor chip and a support portion formed by the protruding resin. The protruding portion of the second semiconductor chip is supported by the support portion from under. Thus, in a semiconductor device having a plurality of laminated semiconductor chips in an attempt to achieve a high density, even when, from a semiconductor chip stacked on a circuit substrate, one portion of a semiconductor chip stacked thereon protrudes, it is possible to carry out a better wire bonding process on electrodes formed on the protruding portion.



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